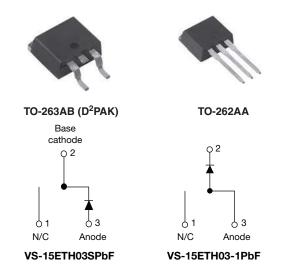


**Vishay Semiconductors** 

# Hyperfast Rectifier, 15 A FRED Pt<sup>®</sup>



PRODUCT SUMMARY							
Package	TO-263AB (D <sup>2</sup> PAK), TO-262AA						
I <sub>F(AV)</sub>	15 A						
V <sub>R</sub>	300 V						
V <sub>F</sub> at I <sub>F</sub>	0.85 V						
t <sub>rr</sub> (typ.)	40 ns						
T <sub>J</sub> max.	175 °C						
Diode variation	Single diode						

### **FEATURES**

- · Hyperfast recovery time
- Low forward voltage drop
- Low leakage current
- 175 °C operating junction temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 gualified
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

### **DESCRIPTION / APPLICATIONS**

Vishay Semiconductors 300 V series are the state of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diodes in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS			
Repetitive peak reverse voltage	V <sub>RRM</sub>		300	V			
Average rectified forward current	I <sub>F(AV)</sub>	T <sub>C</sub> = 142 °C	15	٨			
Non-repetitive peak surge current	I <sub>FSM</sub>	T <sub>J</sub> = 25 °C	140	A			
Operating junction and storage temperatures	TJ, T <sub>Stg</sub>		-65 to +175	°C			

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	I <sub>R</sub> = 100 μA	300	-	-			
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 15 A	-	1.05	1.25	V		
		I <sub>F</sub> = 15 A, T <sub>J</sub> = 125 °C	-	0.85	1.00			
	I <sub>R</sub>	$V_{R} = V_{R}$ rated	-	0.05	40			
Reverse leakage current		$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	12	400	μA		
Junction capacitance	CT	V <sub>R</sub> = 300 V	-	45	-	pF		
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	8	-	nH		

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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_J = 25 \text{ °C}$ unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	TEST CONDITIONS			MAX.	UNITS
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t =$	50 A/ $\mu$ s, V <sub>R</sub> = 30 V	-	-	40	
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	32	-	ns
		T <sub>J</sub> = 125 °C		-	45	-	
Poole recovery ourrent	I <sub>RRM</sub>	T <sub>J</sub> = 25 °C	I <sub>F</sub> = 15 A dI <sub>F</sub> /dt = -200 A/μs V <sub>R</sub> = 200 V	-	2.4	-	А
Peak recovery current		T <sub>J</sub> = 125 °C		-	6.1	-	A
	0	T <sub>J</sub> = 25 °C		-	38	-	nC
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	137	-	nc

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65	-	175	°C	
Thermal resistance, junction to case per leg	R <sub>thJC</sub>	JC		1.02	2.0		
Thermal resistance, junction to ambient per leg	R <sub>thJA</sub>	Typical socket mount	-	-	70	°C/W	
Thermal resistance, case to heatsink	R <sub>thCS</sub>	R <sub>thCS</sub> Mounting surface, flat, smooth and greased		0.2	-		
Waisht			-	2.0	-	g	
Weight			-	0.07	-	oz.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
		Case style D <sup>2</sup> PAK	15ETH03S				
Marking device		Case style TO-262	15ETH03-1				

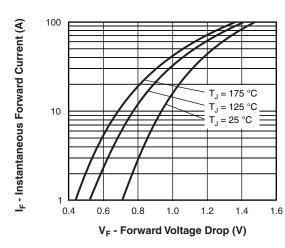


Fig. 1 - Typical Forward Voltage Drop Characteristics

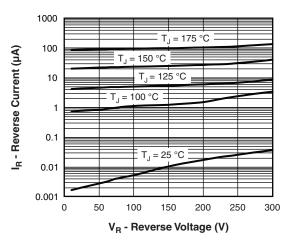


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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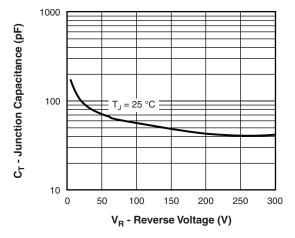


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

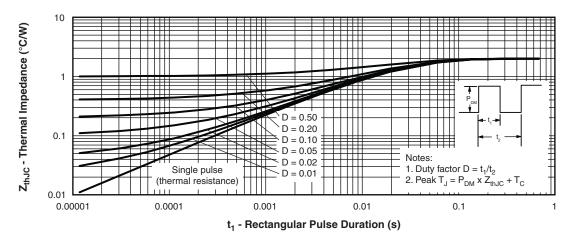


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics

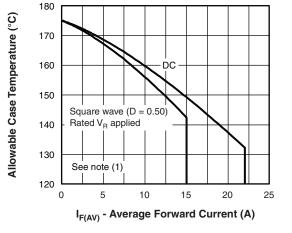


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

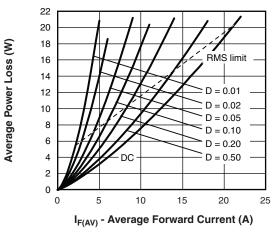


Fig. 6 - Forward Power Loss Characteristics

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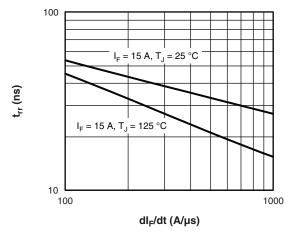


Fig. 7 - Typical Reverse Recovery Time vs. dI<sub>F</sub>/dt

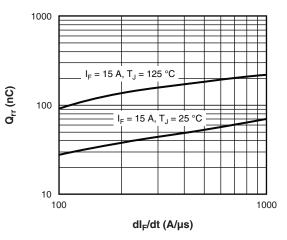


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt



- <sup>(1)</sup> Formula used:  $T_C = T_J (Pd + Pd_{REV}) \times R_{thJC};$  $Pd = Forward power loss = I_{TAVA} \times V_{TAVA} = 1 (I_{TAVA}/D) (see$
- $\begin{array}{l} \mbox{Pd} = \mbox{Forward power loss} = \mbox{I}_{F(AV)} \times \mbox{V}_{FM} \mbox{ at } (I_{F(AV)}/D) \mbox{ (see fig. 6);} \\ \mbox{Pd}_{REV} = \mbox{Inverse power loss} = \mbox{V}_{R1} \times \mbox{I}_{R} \mbox{ (1 D); } I_R \mbox{ at } V_{R1} = \mbox{Rated } V_R \end{array}$

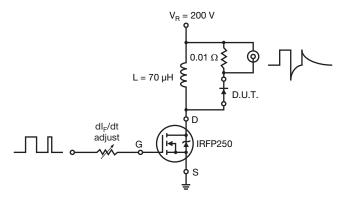


Fig. 9 - Reverse Recovery Parameter Test Circuit



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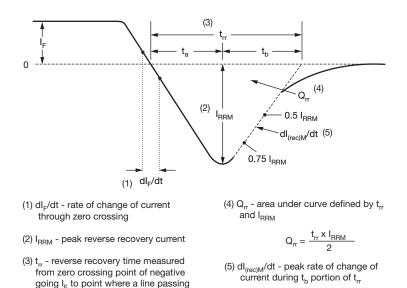
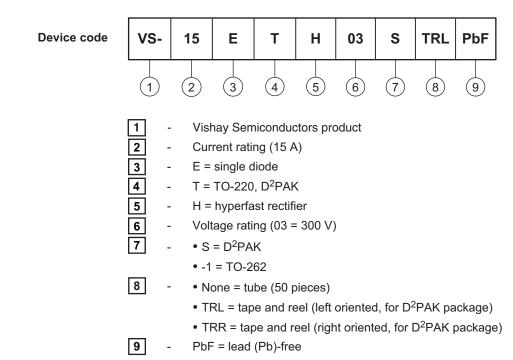


Fig. 10 - Reverse Recovery Waveform and Definitions

through 0.75  $I_{\text{RRM}}$  and 0.50  $I_{\text{RRM}}$  extrapolated to zero current.

#### **ORDERING INFORMATION TABLE**



LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?95014					
Part marking information	www.vishay.com/doc?95008					
Packaging information	www.vishay.com/doc?95032					

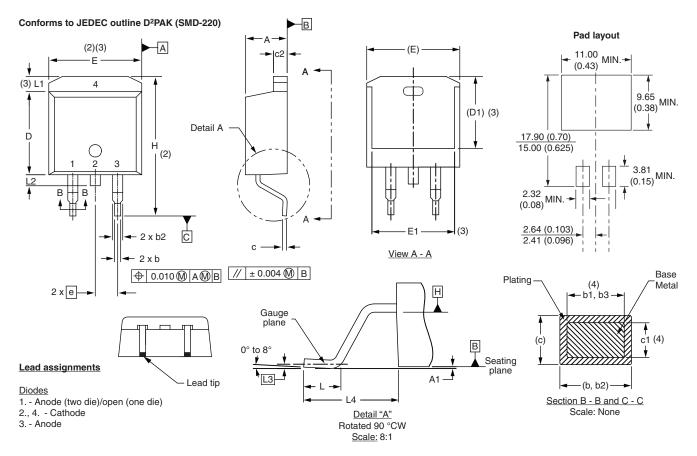
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### D<sup>2</sup>PAK, TO-262



### DIMENSIONS - D<sup>2</sup>PAK in millimeters and inches

SHA

SYMBOL	MILLIN	IETERS	INCHES		NOTES	
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	
А	4.06	4.83	0.160	0.190		
A1	0.00	0.254	0.000	0.010		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
с	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2	

CVMDOI			NOTES		
SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54 BSC		0.100	BSC	
Н	14.61	15.88	0.575	0.625	
L	1.78	2.79	0.070	0.110	
L1	-	1.65	-	0.066	3
L2	1.27	1.78	0.050	0.070	
L3	0.25	BSC	0.010	BSC	
L4	4.78	5.28	0.188	0.208	
L4	4.70	5.20	0.100	0.200	

INCHES

NOTES

MILLIMETERS

<sup>(7)</sup> Outline conforms to JEDEC outline TO-263AB

#### Notes

<sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5 M-1994

<sup>(2)</sup> Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

- <sup>(3)</sup> Thermal pad contour optional within dimension E, L1, D1 and E1
- <sup>(4)</sup> Dimension b1 and c1 apply to base metal only
- <sup>(5)</sup> Datum A and B to be determined at datum plane H

<sup>(6)</sup> Controlling dimension: inch

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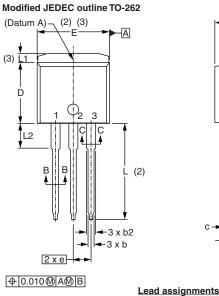
# **Outline Dimensions**

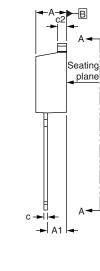
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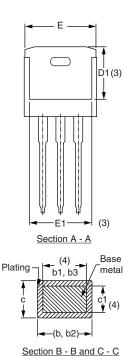
D<sup>2</sup>PAK, TO-262



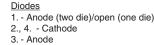
### DIMENSIONS - TO-262 in millimeters and inches

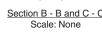






Lead tip





(6) Outline conform to JEDEC TO-262 except A1 (maximum), b (minimum) and D1 (minimum) where dimensions derived the

actual package outline

SYMBOL	MILLIMETERS		INC	NOTES	
STWDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190	
A1	2.03	3.02	0.080	0.119	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
С	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
e	2.54 BSC		0.100	BSC	
L	13.46	14.10	0.530	0.555	
L1	-	1.65	-	0.065	3
L2	3.56	3.71	0.140	0.146	

#### Notes

- <sup>(1)</sup> Dimensioning and tolerancing as per ASME Y14.5M-1994
- <sup>(2)</sup> Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- <sup>(3)</sup> Thermal pad contour optional within dimension E, L1, D1 and E1
- <sup>(4)</sup> Dimension b1 and c1 apply to base metal only

<sup>(5)</sup> Controlling dimension: inches

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